Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Supporting Information

An electric field and strain tunable band gap in the germanene/ZnSe heterostructure

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Contents:

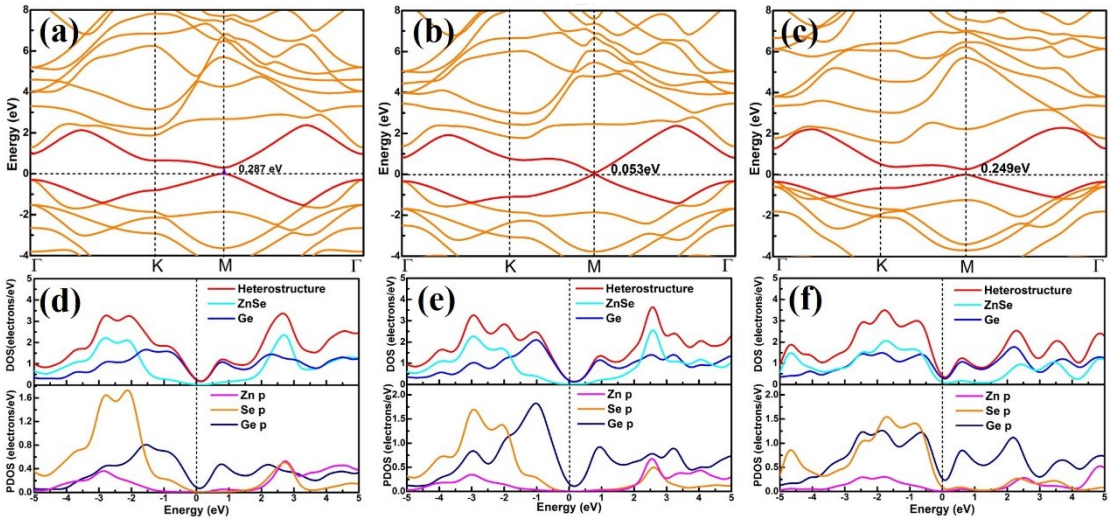

Figure S1: The electronic band structures of (a) AAI, (b) ABI, and (c) ABII patterns, respectively. (d), (e) and (f) the total and partial density of states (DOS & PDOS) of three patterns, respectively.

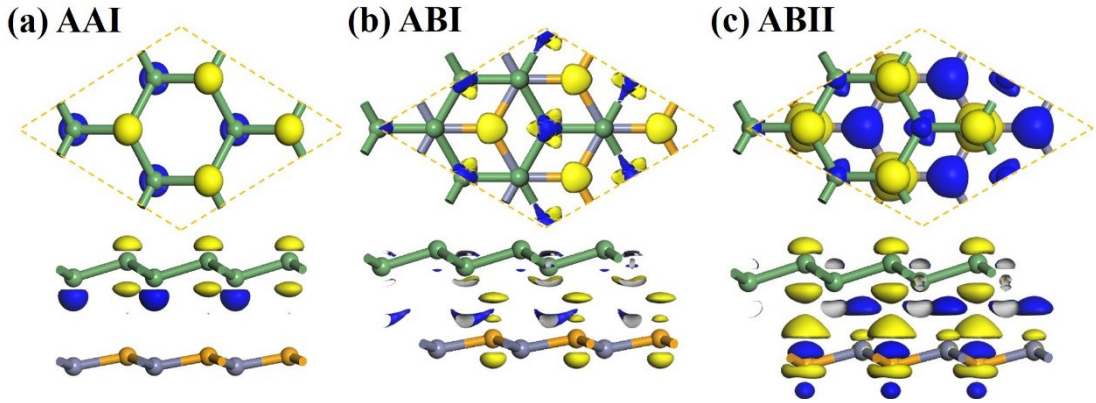

Figure S2: Charge density difference (CDD) of (a)AAI, (b) ABI and (c) ABII patterns in germanene/ZnSe heterostructures. The isosurface value is 0.003 e $Å^{-3}$.